

WEST

Freeform Search

Database:

US Patents Full-Text Database
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Term:**Display:** **Documents in Display Format:** **Starting with Number** **Generate:** ☐ Hit List ☒ Hit Count ☐ Side by Side ☐ Image**Search****Clear****Help****Logout****Interrupt****Main Menu****Show S Numbers****Edit S Numbers****Preferences****Cases**

Search History

DATE: Thursday, October 30, 2003 [Printable Copy](#) [Create Case](#)

<u>Set Name</u> side by side	<u>Query</u>	<u>Hit Count</u>	<u>Set Name</u> result set
<i>DB=USPT,PGPB,JPAB,EPAB,DWPI,TDBD; PLUR=YES; OP=OR</i>			
<u>L16</u>	l14 not l15	69	<u>L16</u>
<u>L15</u>	l8 same l14	24	<u>L15</u>
<u>L14</u>	l6 near10 l11	93	<u>L14</u>
<u>L13</u>	l5 near10 l11	5	<u>L13</u>
<u>L12</u>	l9 near10 l11	4	<u>L12</u>
<u>L11</u>	rate or growthrate	1865502	<u>L11</u>
<u>L10</u>	l7 same l9	85	<u>L10</u>
<u>L9</u>	l6 adj5 l8	214	<u>L9</u>
<u>L8</u>	buffer	618739	<u>L8</u>
<u>L7</u>	rate or thick\$4	3387419	<u>L7</u>
<u>L6</u>	l1 or l5	3066	<u>L6</u>
<u>L5</u>	l4 adj3 nitride	769	<u>L5</u>
<u>L4</u>	aluminum adj gallium	8834	<u>L4</u>
<u>L3</u>	l1 or l2	991486	<u>L3</u>
<u>L2</u>	gallium adh aluminum	990594	<u>L2</u>
<u>L1</u>	algan or gaaln	2700	<u>L1</u>

END OF SEARCH HISTORY

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End of Result Set



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L15: Entry 24 of 24

File: DWPI

Mar 15, 2002

DERWENT-ACC-NO: 2002-447374

DERWENT-WEEK: 200248

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TITLE: Formation of nitride group semiconductor layer for semiconductor element, involves forming semiconductor layer of mixed nitride of aluminum, boron, indium, thallium and gallium, on buffer layer formed on substrate

Basic Abstract Text (1):

NOVELTY - The buffer layer (2) comprising aluminum gallium nitride is grown on a substrate (1), at a growth rate of more than 7 Angstrom /second. A nitride group semiconductor layer (3) comprising a mixed nitride of aluminum, boron, indium, thallium and gallium, is grown on the buffer layer.

Equivalent Abstract Text (1):

NOVELTY - The buffer layer (2) comprising aluminum gallium nitride is grown on a substrate (1), at a growth rate of more than 7 Angstrom /second. A nitride group semiconductor layer (3) comprising a mixed nitride of aluminum, boron, indium, thallium and gallium, is grown on the buffer layer.